imall

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NPN SILICON TRANSISTOR | NE856M03

FEATURES

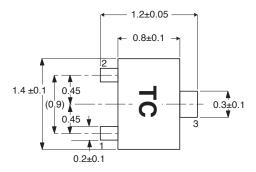
- NEW M03 PACKAGE:
 - · Smallest transistor outline package available
 - · Low profile/0.59 mm package height
 - Flat lead style for better RF performance
- LOW NOISE FIGURE: NF = 1.4 dB at 1 GHz
- HIGH COLLECTOR CURRENT: ICMAX = 100 mA

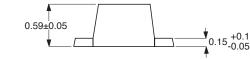
DESCRIPTION

NEC's NE856M03 transistor is designed for low cost amplifier and oscillator applications. Low noise figure, high gain and high current capability equate to wide dynamic range and excellent linearity. NEC's new low profile/flat lead style "M03" package is ideal for today's portable wireless applications. The NE856 is also available in chip, Micro-x, and eight different low cost plastic surface mount package styles.

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE M03





PIN CONNECTIONS

- 1. Emitter
- 2. Base
- 3. Collector

ELECTRICAL CHARACTERISTICS (TA = 25°C)

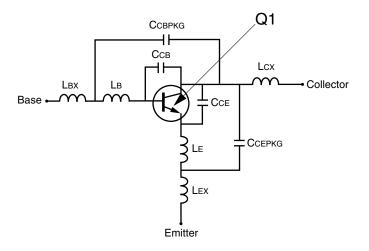
	PART NUMBER EIAJ ¹ REGISTERED NUMBER PACKAGE OUTLINE	ISTERED NUMBER 2SC5432			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	МАХ
f⊤	Gain Bandwidth at VCE = 3 V, IC = 7 mA, f = 1 GHz	GHz	3.0	4.5	
NF	Noise Figure at VcE = 3 V, Ic = 7 mA, f = 1 GHz	dB		1.4	2.5
IS21El ²	Insertion Power Gain at VCE = 3 V, IC = 7 mA, f = 1 GHz	dB	7.0	10.0	
hfe ²	Forward Current Gain at VcE = 3 V, Ic = 7 mA		80		145
Ісво	Collector Cutoff Current at VCB = 10 V, IE = 0	μΑ			1.0
Іево	Emitter Cutoff Current at VEB = 1 V, IC = 0	μΑ			1.0
Cre ³	Feedback Capacitance at $V_{CB} = 3 V$, $I_E = 0$, $f = 1 MHz$	pF		0.7	1.5

Notes:

- 1. Electronic Industrial Association of Japan.
- 2. Pulsed measurement, pulse width \leq 350 µs, duty cycle \leq 2 %.
- 3. Capacitance is measured with emitter and case connected to the guard terminal at the bridge.

NONLINEAR MODEL

SCHEMATIC



BJT NONLINEAR MODEL PARAMETERS (1)

Parameters	Q1	Parameters	Q1
IS	9.2e-16	MJC	0.55
BF	110.3	XCJC	0.3
NF	1.01	CJS	0
VAF	18	VJS	0.75
IKF	1	MJS	0
ISE	4.89e-9	FC	0.5
NE	4.37	TF	4e-12
BR	10.08	XTF	30
NR	1.0	VTF	0.69
VAR	8	ITF	0.06
IKR	0.03	PTF	0
ISC	3.32e-11	TR	1e-9
NC	3.95	EG	1.11
RE	0.33	XTB	0
RB	1.26	XTI	3
RBM	2	KF	1.56e-18
IRB	0.05	AF	1.49
RC	6.63		
CJE	2.8e-12		
VJE	1.3		
MJE	0.5		
CJC	1.1e-12		
VJC	0.7		

UNITS

Parameter	Units
time	seconds
capacitance	farads
inductance	henries
resistance	ohms
voltage	volts
current	amps

ADDITIONAL PARAMETERS

Parameters	856M03
Ссв	0.087e-12
CCE	0.16e-12
Lв	0.5e-9
LE	0.6e-9
Ссвркд	0.08e-12
Ссеркд	0.08e-12
LBX	0.12e-9
Lcx	0.10e-9
Lex	0.12e-9

MODEL RANGE

Frequency:	0.1 to 4.0 GHz	
Bias:	VCE = 0.5 V to 10 V,	Ic = 0.5 mA to 10 mA
Date:	11/98	

(1) Gummel-Poon Model

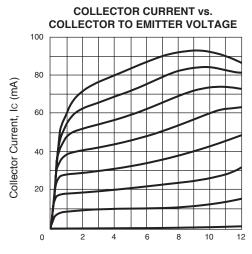
SYMBOLS	PARAMETERS	UNITS	RATINGS
Vсво	Collector to Base Voltage	V	20
VCEO	Collector to Emitter Voltage	V	12
Vebo	Emitter to Base Voltage	V	3
lc	Collector Current	mA	100
Рт	Total Power Dissipation	mW	125
TJ	Junction Temperature	°C	150
Тѕтс	Storage Temperature	°C	-65 to +150

ABSOLUTE MAXIMUM RATINGS¹ (TA = 25°C)

Note:

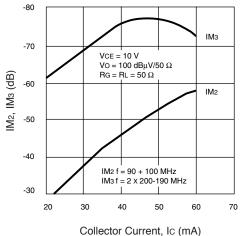
1. Operation in excess of any one of these parameters may result in permanent damage.

TYPICAL PERFORMANCE CURVES (TA = 25°C)



Collector to Emitter Voltage, VCE (V)

NE856M03 INTERMODULATION DISTORTION vs. COLLECTOR CURRENT



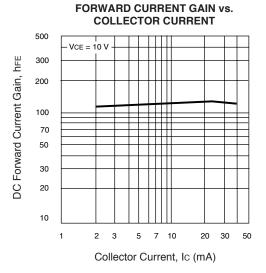
Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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DATA SUBJECT TO CHANGE WITHOUT NOTICE
Internet: http://WWW.CEL.COM
06/10/2002

ORDERING INFORMATION

PART NUMBER	QUANTITY
NE856M03-A	
NE856M03-T1-A	





4590 Patrick Henry Drive Santa Clara, CA 95054-1817 Telephone: (408) 919-2500 Facsimile: (408) 988-0279

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
РВВ	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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In no event shall CEL's liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.